

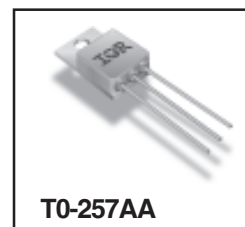
**RADIATION HARDENED
 POWER MOSFET
 THRU-HOLE (TO-257AA)**

**IRHY597130CM
 JANSR2N7547T3
 100V, P-CHANNEL
 REF: MIL-PRF-19500/712**



Product Summary

Part Number	Radiation Level	RDS(on)	ID	QPL Part Number
IRHY597130CM	100K Rads (Si)	0.215Ω	-12.5A	JANSR2N7547T3
IRHY593130CM	300K Rads (Si)	0.215Ω	-12.5A	JANSF2N7547T3



International Rectifier's R5™ technology provides high performance power MOSFETs for space applications. These devices have been characterized for Single Event Effects (SEE) with useful performance up to an LET of 80 (MeV/(mg/cm²)). The combination of low RDS(on) and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features:

- Single Event Effect (SEE) Hardened
- Ultra Low RDS(on)
- Low Total Gate Charge
- Proton Tolerant
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Ceramic Package
- Light Weight
- ESD Rating: Class 1C per MIL-STD-750, Method

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
ID @ VGS = -12V, TC = 25°C	Continuous Drain Current	-12.5	A
ID @ VGS = -12V, TC = 100°C	Continuous Drain Current	-8.0	
IDM	Pulsed Drain Current ①	-50	
PD @ TC = 25°C	Max. Power Dissipation	75	W
	Linear Derating Factor	0.6	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	94	mJ
IAR	Avalanche Current ①	-12.5	A
EAR	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-4.3	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Lead Temperature	300 (0.063in/1.6mm from case for 10s)	
	Weight	4.3 (Typical)	g

For footnotes refer to the last page

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	-100	—	—	V	V _{GS} = 0V, I _D = -1.0mA
ΔBV _{DSS} /ΔT _J	Temperature Coefficient of Breakdown Voltage	—	-0.12	—	V/°C	Reference to 25°C, I _D = -1.0mA
R _{DSON}	Static Drain-to-Source On-State Resistance	—	—	0.215	Ω	V _{GS} = -12V, I _D = -8.0A ④
V _{GS(th)}	Gate Threshold Voltage	-2.0	—	-4.0	V	V _{DS} = V _{GS} , I _D = -1.0mA
g _{fs}	Forward Transconductance	6.3	—	—	S	V _{DS} = -15V, I _{DS} = -8.0A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	-10	μA	V _{DS} = -80V, V _{GS} = 0V
		—	—	-25		V _{DS} = -80V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V _{GS} = -20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	100		V _{GS} = 20V
Q _g	Total Gate Charge	—	—	40	nC	V _{GS} = -12V, I _D = -12.5A V _{DS} = -50V
Q _{gs}	Gate-to-Source Charge	—	—	16		
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	11		
t _{d(on)}	Turn-On Delay Time	—	—	25	ns	V _{DD} = -50V, I _D = -12.5A, V _{GS} = -12V, R _G = 7.5Ω,
t _r	Rise Time	—	—	55		
t _{d(off)}	Turn-Off Delay Time	—	—	30		
t _f	Fall Time	—	—	100		
L _S + L _D	Total Inductance	—	6.8	—	nH	Measured from drain lead (6mm/0.25in. from package) to source lead (6mm/0.25in. from package)
C _{iss}	Input Capacitance	—	1350	—	pF	V _{GS} = 0V, V _{DS} = -25V f = 1.0MHz
C _{oss}	Output Capacitance	—	330	—		
C _{rss}	Reverse Transfer Capacitance	—	20	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-12.5	A	T _j = 25°C, I _S = -12.5A, V _{GS} = 0V ④
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	-50		
V _{SD}	Diode Forward Voltage	—	—	-5.0	V	T _j = 25°C, I _F = -12.5A, di/dt ≤ -100A/μs
t _{rr}	Reverse Recovery Time	—	—	150	ns	V _{DD} ≤ -25V ④
Q _{RR}	Reverse Recovery Charge	—	—	620	nC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	1.67	°C/W	Typical Socket Mount
R _{thJA}	Junction-to-Ambient	—	—	80		

Note: Corresponding Spice and Saber models are available on International Rectifier website.

For footnotes refer to the last page

Radiation Characteristics

IRHY597130CM, JANSR2N7547T3

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	100K Rads(Si) ¹		300KRads(Si) ²		Units	Test Conditions
		Min	Max	Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	-100	—	-200	—	V	V _{GS} = 0V, I _D = -1.0mA
V _{GS(th)}	Gate Threshold Voltage	-2.0	-4.0	-2.0	-5.0		V _{GS} = V _{DS} , I _D = -1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	-100	—	-100	nA	V _{GS} = -20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	100	—	100		V _{GS} = 20 V
I _{DSS}	Zero Gate Voltage Drain Current	—	-10	—	-10	μA	V _{DS} = -80V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source ④	—	0.205	—	0.205	Ω	V _{GS} = -12V, I _D = -8.0A
	On-State Resistance (TO-3)						
R _{DS(on)}	Static Drain-to-Source ④	—	0.215	—	0.215	Ω	V _{GS} = -12V, I _D = -8.0A
	On-State Resistance (TO-257AA)						
V _{SD}	Diode Forward Voltage ④	—	-5.0	—	-5.0	V	V _{GS} = 0V, I _S = -12.5A

1. Part number IRHY597130CM, JANSR2N7547T3

2. Part number IRHY593130CM, JANSF2N7547T3

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	VDS (V)				
			@VGS = 0V	@VGS = 5V	@VGS = 10V	@VGS = 15V	@VGS = 20V
38 ± 5%	270 ± 7.5%	35 ± 7.5%	-100	-100	-100	-100	-100
61 ± 5%	330 ± 7.5%	30 ± 7.5%	-100	-100	-100	-100	-25
84 ± 5%	350 ± 7.5%	28 ± 7.5%	-100	-100	-100	-30	-

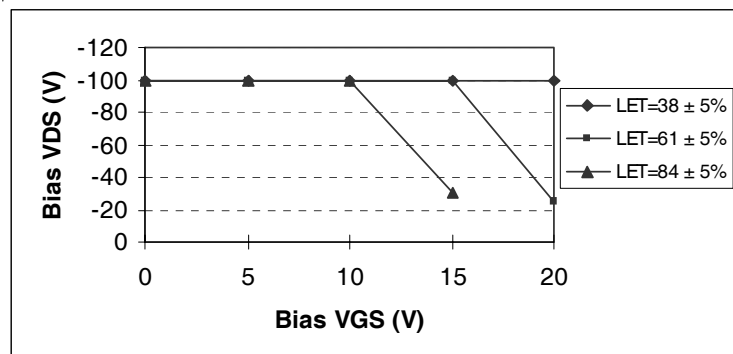


Fig a. Typical Single Event Effect, Safe Operating Area

For footnotes refer to the last page

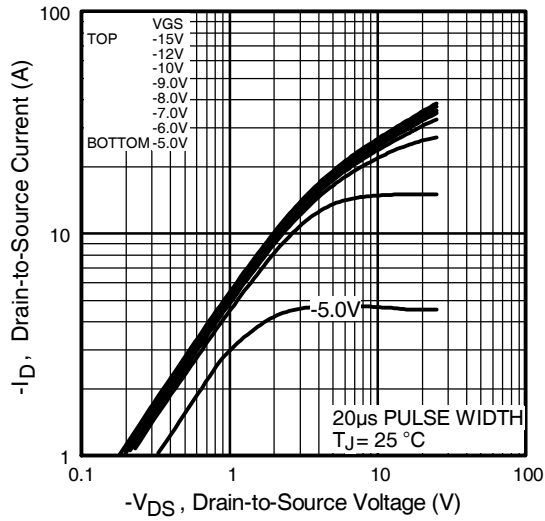


Fig 1. Typical Output Characteristics

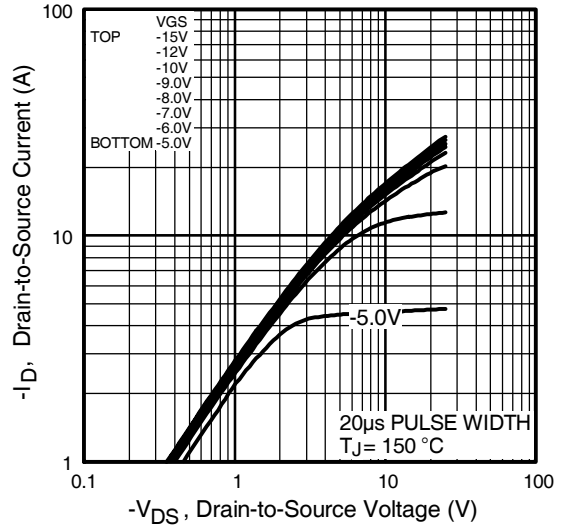


Fig 2. Typical Output Characteristics

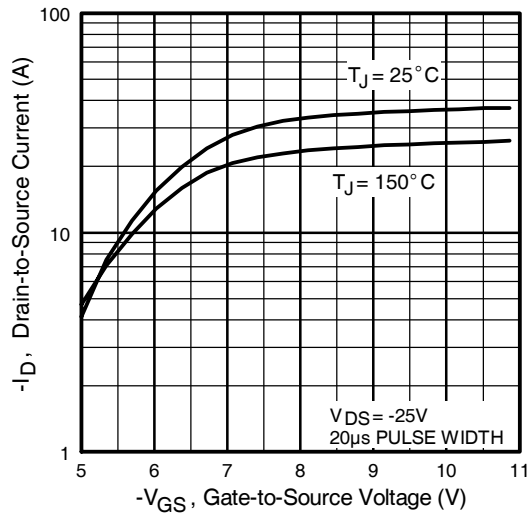


Fig 3. Typical Transfer Characteristics

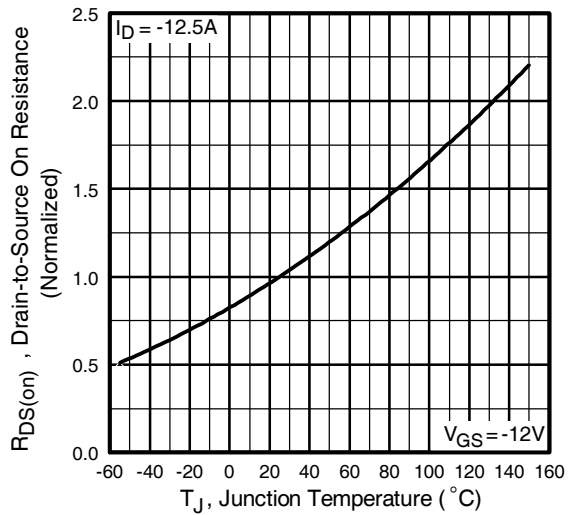


Fig 4. Normalized On-Resistance Vs. Temperature

Pre-Irradiation

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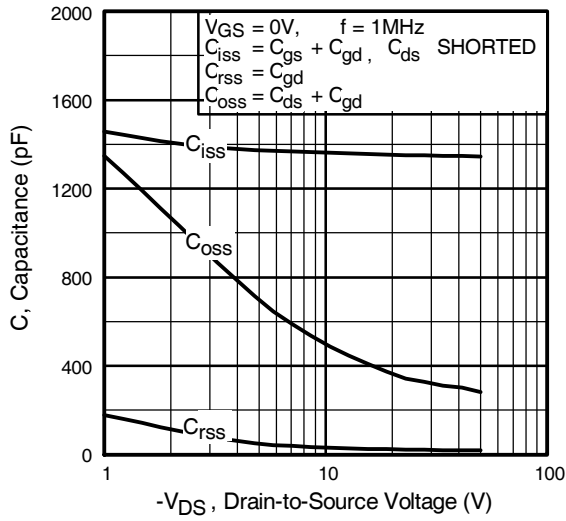


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

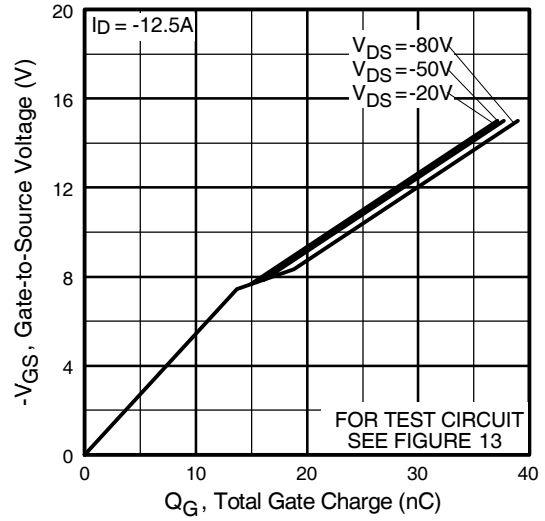


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

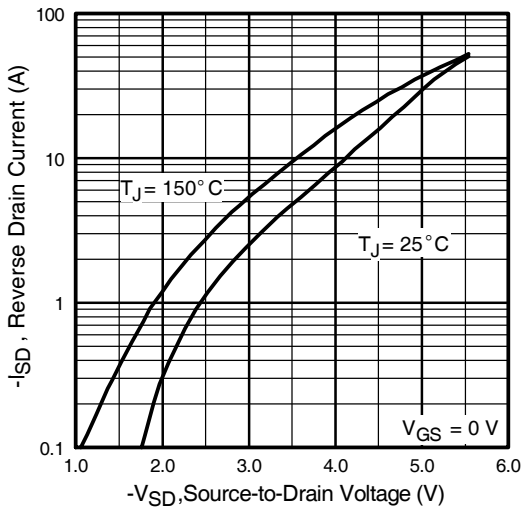


Fig 7. Typical Source-Drain Diode Forward Voltage

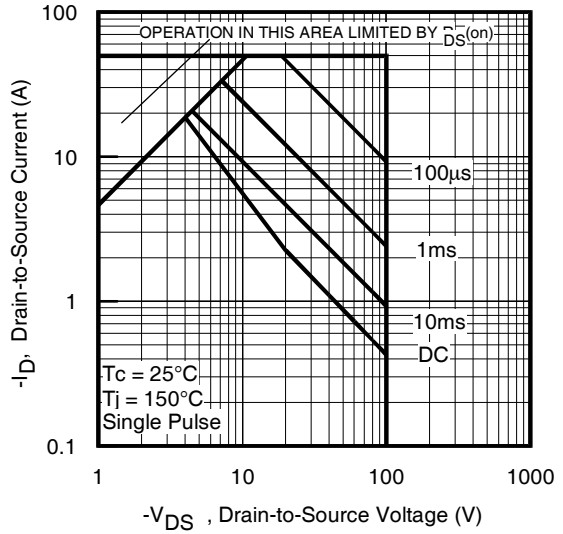


Fig 8. Maximum Safe Operating Area

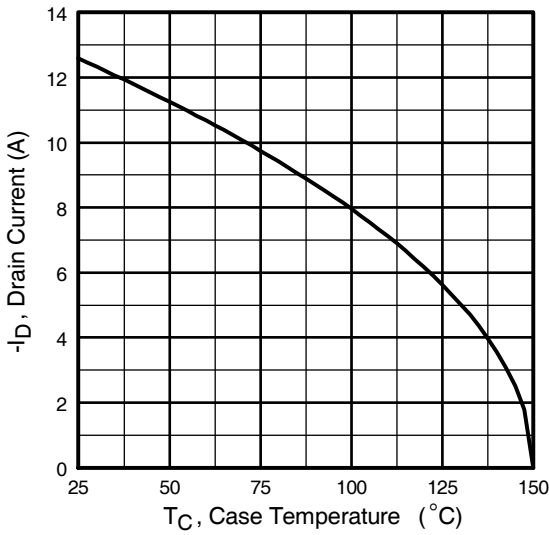


Fig 9. Maximum Drain Current Vs. Case Temperature

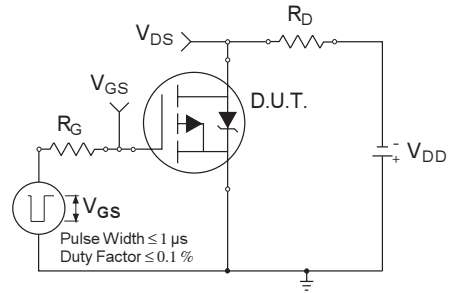


Fig 10a. Switching Time Test Circuit

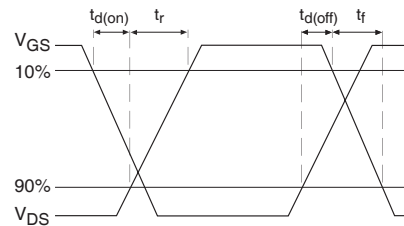


Fig 10b. Switching Time Waveforms

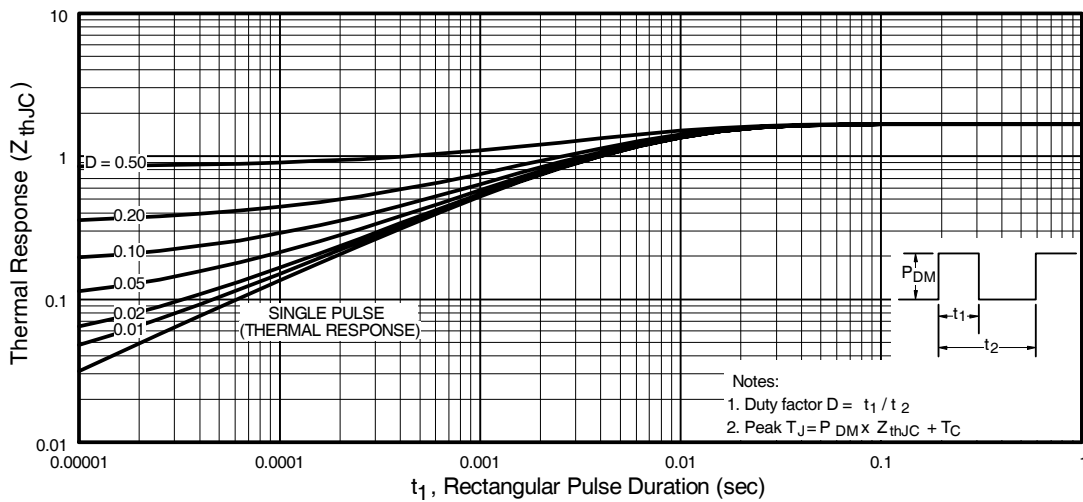


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Pre-Irradiation

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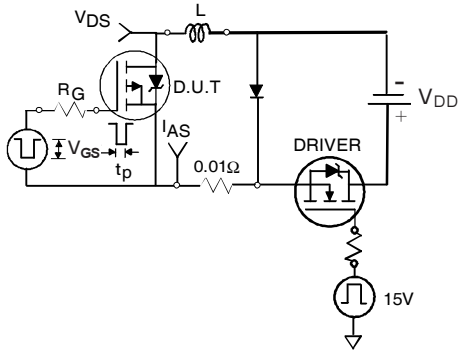


Fig 12a. Unclamped Inductive Test Circuit

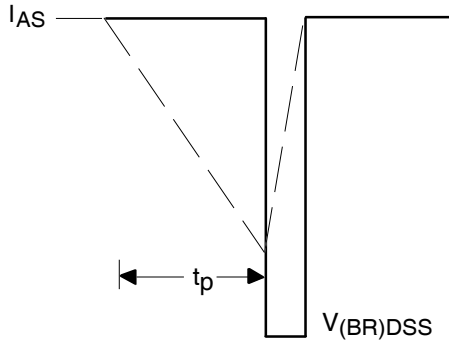


Fig 12b. Unclamped Inductive Waveforms

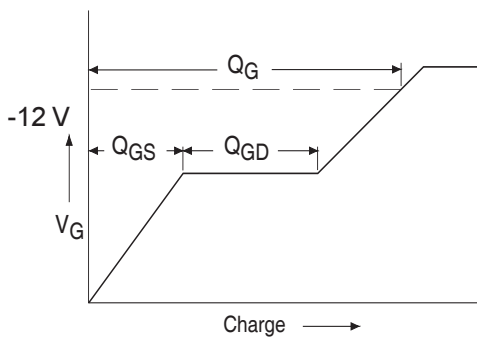


Fig 13a. Basic Gate Charge Waveform

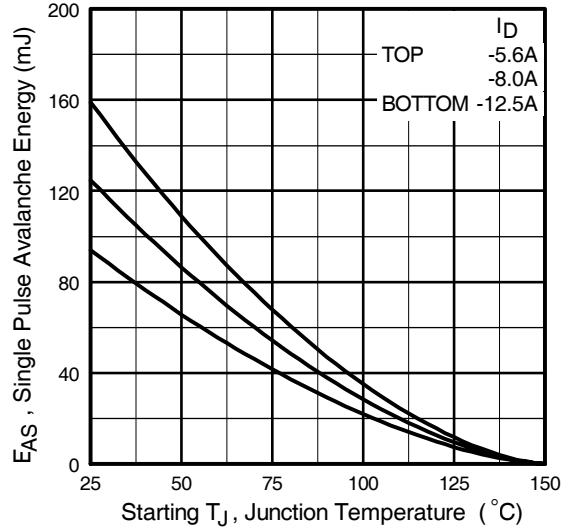


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

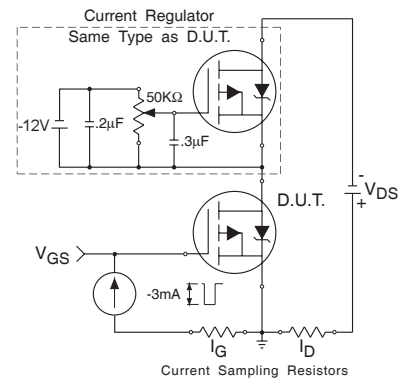


Fig 13b. Gate Charge Test Circuit

